

Bipolar Transistor -160 V, -1 A, Low V_{CE}(sat), PNP Single NSVT1418L

This device is bipolar junction transistor featuring high current, low saturation voltage, and high speed switching.

Suitable for automotive applications. AEC-Q101 qualified and PPAP capable.

Features

- Large Current Capacitance
- Low Collector to Emitter Saturation Voltage
- High Speed Switching
- High Allowable Power Dissipation
- AEC-Q101 Qualified and PPAP Capable
- Pb-Free, Halogen Free and RoHS Compliant
- Ultra Small Package Facilitates Miniaturization in End Products

Typical Applications

- High Side Switch
- Lighting, Infotainment

ABSOLUTE MAXIMUM RATINGS at $T_A = 25$ °C

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V _{CBO}	-180	V
Collector to Emitter Voltage	V _{CEO}	-160	V
Emitter to Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	-1	Α
Collector Current (Pulse)	I _{CP}	-2	Α
Collector Dissipation (Note 1)	P _C	0.42	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	–55 to +150	°C

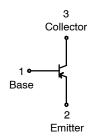
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

1. Surface mounted on ceramic substrate. (250 mm² x 0.8 mm)



ELECTRICAL CONNECTION



MARKING DIAGRAM



CMM = Specific Device Code M = Single Digit Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

			Value			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	$V_{CB} = -120 \text{ V}, I_E = 0 \text{ A}$			-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -4 \text{ V}, I_{C} = 0 \text{ A}$			-0.1	μΑ
DC Current Gain	h _{FE1}	V _{CE} = -5 V, I _C = -100 mA	100		400	
	h _{FE2}	$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	90			
Gain-Bandwidth Product	f _T	V _{CE} = -10 V, I _C = -50 mA		120		MHz
Output Capacitance	Cob	V _{CB} = -10 V, f = 1 MHz		11		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)1	$I_C = -250 \text{ mA},$ $I_B = -25 \text{ mA}$		-0.1	-0.5	V
	V _{CE} (sat)2	$I_C = -250 \text{ mA},$ $I_B = -50 \text{ mA}$		-0.08	-0.13	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	$I_C = -250 \text{ mA},$ $I_B = -25 \text{ mA}$		-0.8	-1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_C = -10 \mu\text{A}, \ I_E = 0 \text{A}$	-180			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -1$ mA, $R_{BE} = \infty$	-160			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	$I_E = -10 \mu A,$ $I_C = 0 A$	-6			V
Turn-On Time	t _{on}	See Figure 1		90		ns
Storage Time	t _{stg}	1		1000		ns
Fall Time	t _f]		70		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

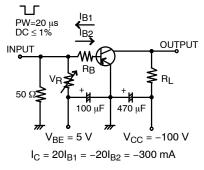
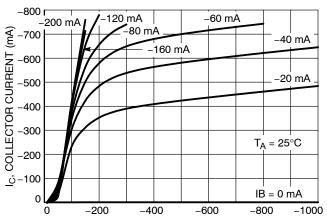


Figure 1. Switching Time Test Circuit

TYPICAL CHARACTERISTICS



V_{CE}, COLLECTOR-TO-EMITTER VOLTAGE (mV)

Figure 2. I_C vs. V_{CE}

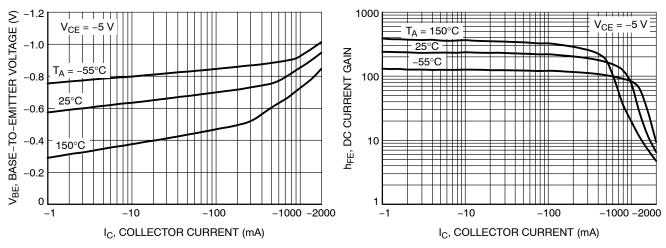


Figure 3. V_{BE} vs. I_{C}

Figure 4. h_{FE} vs. I_C

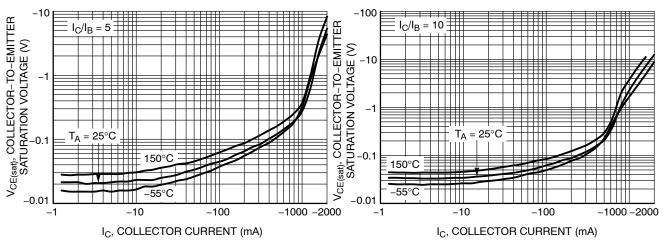


Figure 5. V_{CE(sat)} vs. I_C

Figure 6. V_{CE(sat)} vs. I_C

TYPICAL CHARACTERISTICS

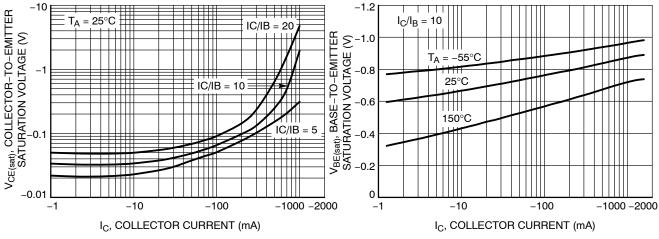


Figure 7. V_{CE(sat)} vs. I_C

Figure 8. V_{BE(sat)} vs. I_C

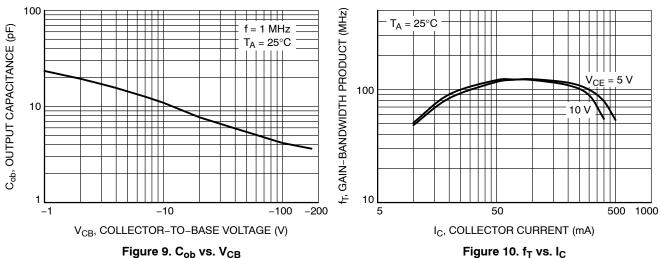


Figure 9. Cob vs. VCB

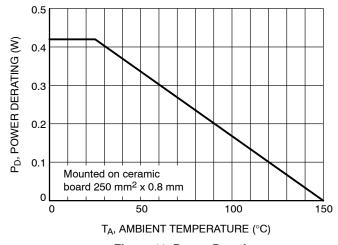


Figure 11. Power Derating

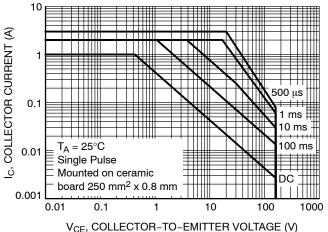


Figure 12. Safe Operating Area

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) †
NSVT1418LT1G	СММ	SOT-23 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

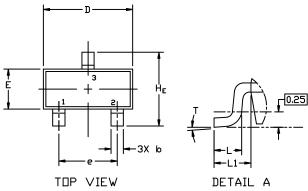




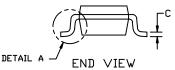
SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10*



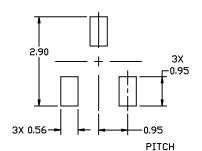


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2		

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2		

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales